# PUA3117 (PU3117)

### Silicon NPN triple diffusion planar type

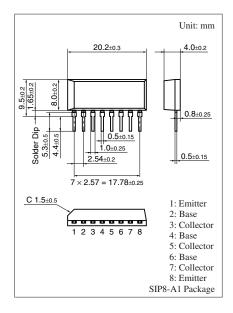
For power amplification and switching

#### Features

- High forward current transfer ratio h<sub>FE</sub>
- $\bullet$  Satisfactory linearity of forward current transfer ratio  $h_{\text{FE}}$
- NPN 3 elements

<b>3</b> - C									
Parameter	Symbol	Rating	Unit						
Collector-base voltage (Emitter open)		V <sub>CBO</sub>	80	V					
Collector-emitter voltage (Base open)		V <sub>CEO</sub>	60	V					
Emitter-base voltage (Collector open)		V <sub>EBO</sub>	6	V					
Collector current		I <sub>C</sub>	3	А					
Peak collector current		I <sub>CP</sub>	6	А					
Base current		IB	1	А					
Collector power dissipation		P <sub>C</sub>	15	W					
	$T_a = 25^{\circ}C$		2.4						
Junction temperature		Tj	150	°C					
Storage temperature		T <sub>stg</sub>	-55 to +150	°C					

#### Absolute Maximum Ratings $T_C = 25^{\circ}C$

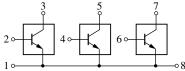


#### Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 25 \text{ mA}, I_{\rm B} = 0$	60			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 80 \text{ V}, I_E = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 40 \text{ V}, I_B = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 6 V, I_C = 0$			100	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 4 V, I_C = 0.5 A$	500		2 5 0 0	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 2$ A, $I_{\rm B} = 0.05$ A			1.0	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 12 \text{ V}, I_C = 0.2 \text{ A}, f = 10 \text{ MHz}$		50		MHz

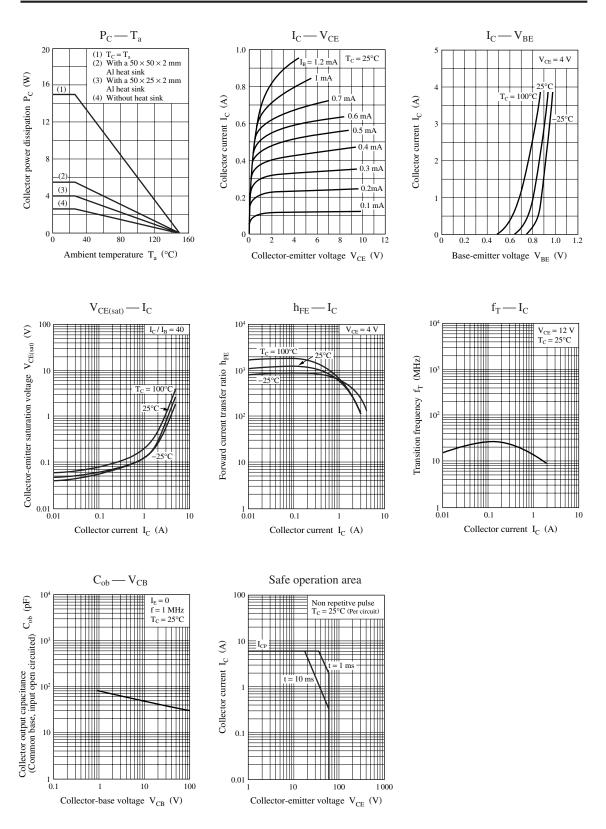
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.





Note) The part number in the parenthesis shows conventional part number.

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